



ZXTP25100CZ

100V PNP MEDIUM POWER TRANSISTOR IN SOT89

Features

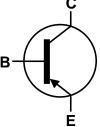
- BV_{CEO} > -100V
- BV_{ECO} > -7V
- I_C = -1A Continuous Collector Current
- I_{CM} = -3A Peak Collector Current
- V_{CE(SAT)} < -225mV @ -1A
- R_{CE(SAT)} = 155mΩ for a Low Equivalent On-Resistance
- Complementary NPN Type: ZXTN25100DZ
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

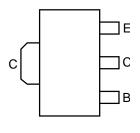
Top View

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.05 grams (Approximate)







Device Symbol

Top View Pin Out

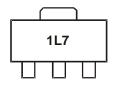
Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTP25100CZTA	AEC-Q101	1L7	7	12	1,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



1L7 = Product Type Marking Code



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	-115	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Collector Voltage (Reverse Blocking)	V _{ECO}	-7	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Current	I _{CM}	-3	Α
Base Current	I _B	-500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1.1 8.8		
Power Dissipation	(Note 6)	P _D	1.8 14.4	W mW/°C	
Linear Derating Factor	(Note 7)		2.4 19.2		
	(Note 8)		4.46 35.7		
	(Note 5)		117		
Thermal Desistance, Junction to Ambient Air	(Note 6)		68		
Thermal Resistance, Junction to Ambient Air	(Note 7)	$R_{ hetaJA}$	51	°C/W	
	(Note 8)		28		
Thermal Resistance, Junction to Lead	(Note 9)	$R_{\theta JL}$	7.95		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

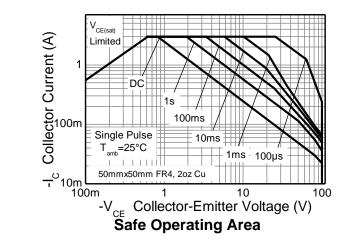
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

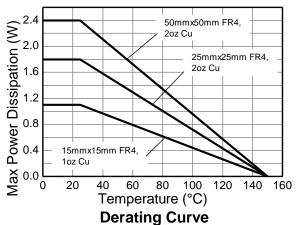
Notes:

- 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 0.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
- 8. Same as Note 7, except the device is measured at t<5 seconds.
- 9. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



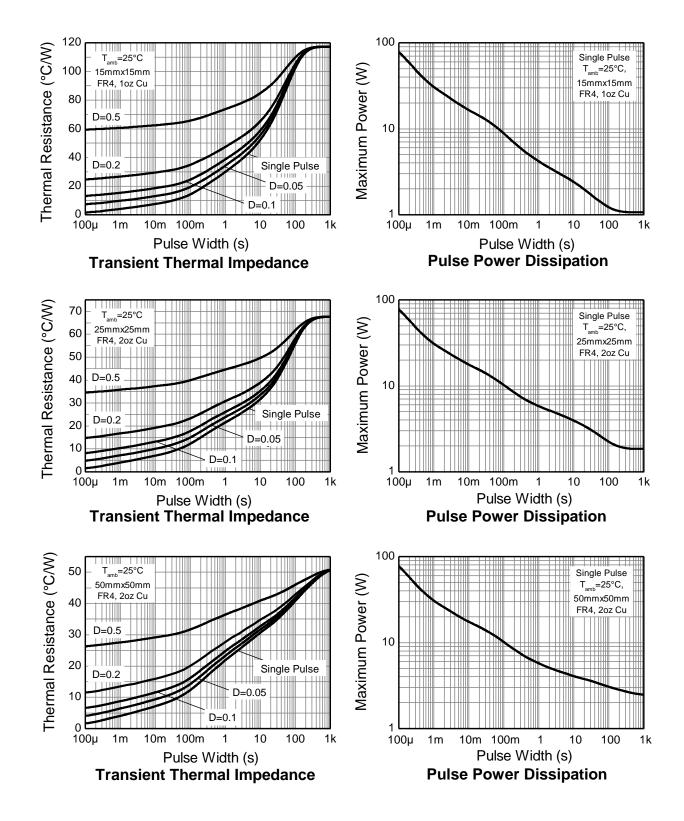
Thermal Characteristics and Derating Information







Thermal Characteristics and Derating Information (Continued)





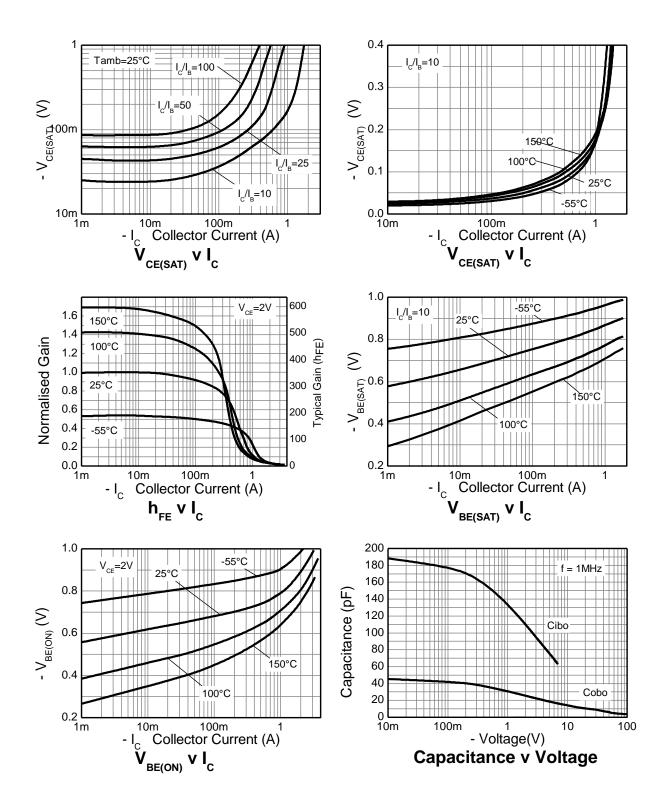
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-115	-180	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-100	-140	_	V	I _C = -10mA
Emitter-Collector Breakdown Voltage (reverse blocking)	BV _{ECX}	-7	-8.3	_	V	I_E = -100μA, R_{BC} <1k Ω or -0.25V > V_{BC} > 0.25V
Emitter-Collector Breakdown Voltage (Reverse Blocking)	BV _{ECO}	-7	-8.8	_	V	I _E = -100μA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.4	_	V	I _E = -100μA
Collector-Base Cutoff Current	I _{CBO}		<-1	-50 -0.5	nA μA	V _{CB} = -115V V _{CB} = -115V, T _A = +100°C
Collector-Emitter Cutoff Current	I _{CEX}	_	_	-100	nA	V_{CE} = -90V, R_{BE} <1k Ω or -0.25V < V_{BE} < 1V
Emitter Cutoff Current	I _{EBO}	_	<1	-50	nA	V _{EB} = -5.6V
DC current transfer Static ratio (Note 11)	h _{FE}	200 180 110 20	350 320 190 35	500 — — —	_	I_{C} = -10mA, V_{CE} = -2V I_{C} = -100mA, V_{CE} = -2V I_{C} = -500mA, V_{CE} = -2V I_{C} = -1A, V_{CE} = -2V
Collector-Emitter Saturation Voltage (Note 11)	VCE(SAT)	_	-140 -80 -180 -155	-210 -115 -315 -225	mV	I _C = -100mA, I _B = -1mA I _C = -500mA, I _B = -50mA I _C = -500mA, I _B = -20mA I _C = -1A, I _B = -100mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(SAT)}	_	-860	-950	mV	I _C = -1A, I _B = -100mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(ON)}	_	-800	-900	mV	I _C = -1A, V _{CE} = -2V
Transitional Frequency	f⊤	_	180	_	MHz	$I_E = -20 \text{mA}, V_{CE} = -15 \text{V}$ f = 100 MHz
Input Capacitance	C _{IBO}		153	_	pF	V _{EB} = -0.5V, f = 1MHz,
Output Capacitance	C _{OBO}		14.1	20	pF	V _{CB} = -10V, f = 1MHz,
Delay Time	t _D	_	15.8	_	ns	
Rise Time	t _R		41	_	ns	$I_{C} = -500 \text{mA}, V_{CC} = -10 \text{V},$
Storage Time	ts	_	411	_	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$
Fall Time	t _F	_	89	_	ns	

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

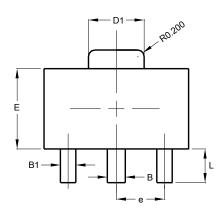


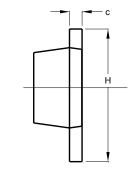


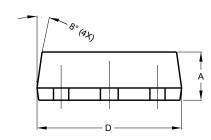
Package Outline Dimensions

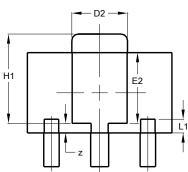
Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89







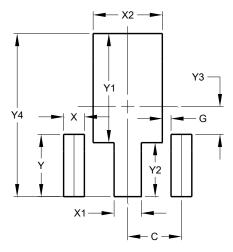


SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	1	1	1.50		
Н	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
Z	0.20	0.40	0.30		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



Dimensions	Value
Dimensions	(in mm)
С	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Υ	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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